

1 Scope

The present specifications shall apply to an FMU-16S,R.

2 Outline

Type	Silicon Diode
Structure	Resin Molded
Applications	High Frequency Rectification

3 Flammability

UL94V-0(Equivalent)

4 Absolute maximum ratings

No.	Item	Symbol	Unit	Rating	Conditions
1	Transient Peak Reverse Voltage	V_{RSM}	V	650	
2	Peak Reverse Voltage	V_{RM}	V	600	
3	Average Forward Current	$I_{F(AV)}$	A	5.0	Refer to derating curve in Section 7
4	Peak Surge Forward Current	I_{FSM}	A	30	10ms. Half sine wave, one shot
5	I^2t Limiting Value	I^2t	A^2s	4.5	$1\text{ ms} \leq t \leq 10\text{ ms}$
6	Junction Temperature	T_j	$^{\circ}C$	-40 to +150	
7	Storage Temperature	T_{stg}	$^{\circ}C$	-40 to +150	

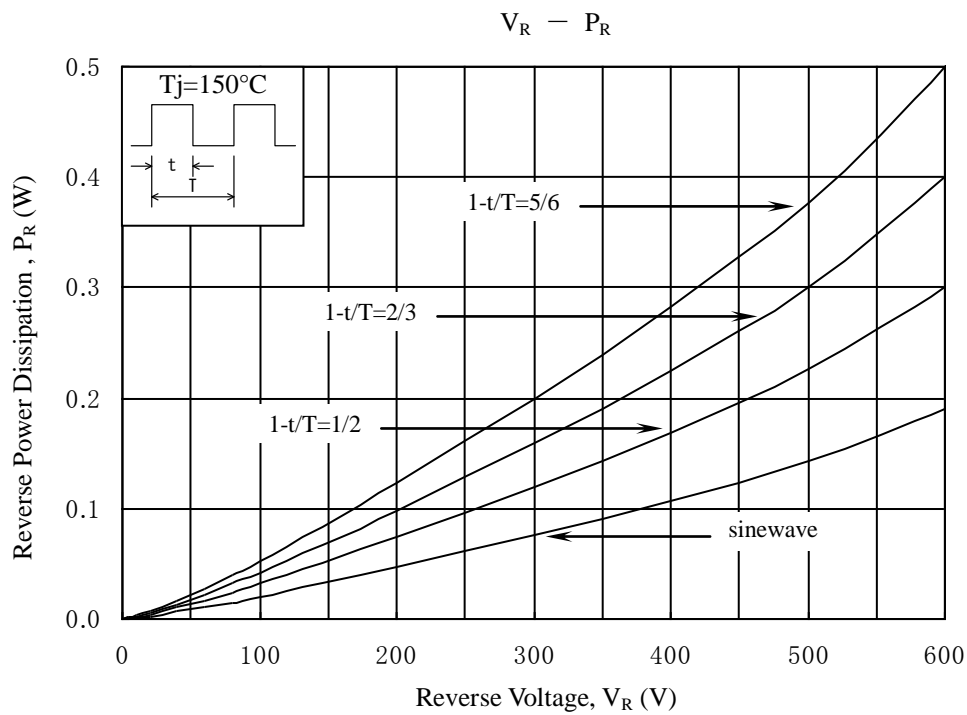
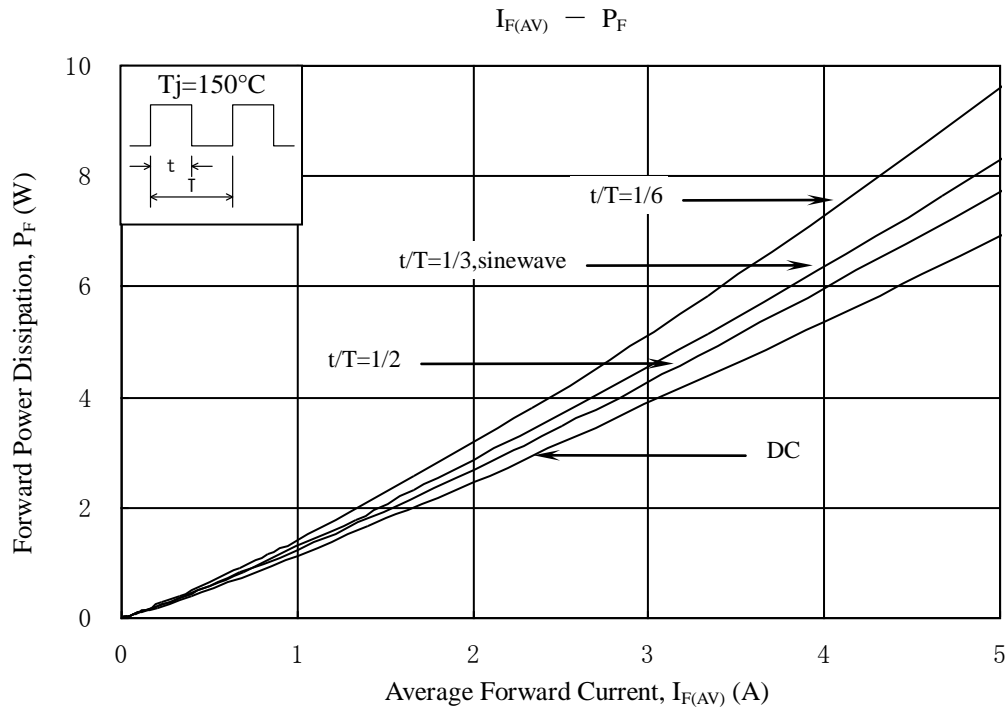
No.1, 2, 4 and 5 show ratings per one chip.

5 Electrical characteristics ($T_a=25^{\circ}C$, unless otherwise specified)

No.	Item	Symbol	Unit	Value	Conditions
1	Forward Voltage Drop	V_F	V	1.5 max.	$I_F=2.5A$
2	Reverse Leakage Current	I_R	μA	50 max.	$V_R=V_{RM}$
3	Reverse Leakage Current Under High Temperature	$H \cdot I_R$	μA	500 max.	$V_R=V_{RM}, T_j=150^{\circ}C$
4	Reverse Recovery Time	t_{rr1}	ns	400 max.	$I_F=I_{RP}=100mA$ 90% Recovery point, $T_j=25^{\circ}C$
		t_{rr2}	ns	180 max.	$I_F=100mA, I_{RP}=200mA$ 75% Recovery point, $T_j=25^{\circ}C$
5	Thermal Resistance	$R_{th(j-c)}$	$^{\circ}C/W$	4.0 max.	Between Junction and case

No.1, 2, 3 and 4 show characteristics per one chip.

6 Characteristics



7 Derating

